Unit: mm

TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT process)

# 2SA1162

## Audio Frequency General Purpose Amplifier Applications

• High voltage and high current:  $V_{\rm CEO}$  = -50 V,  $I_{\rm C}$  = -150 mA (max)

• Excellent hFE linearity: hFE (IC = -0.1 mA)/hFE (IC = -2 mA) = 0.95 (typ.)

• High hfe: hfe = 70 to 400

• Low noise: NF = 1dB (typ.), 10dB (max)

• Complementary to 2SC2712

• Small package

## **Absolute Maximum Ratings (Ta = 25°C)**

Characteristics	Symbol	Rating	Unit	
Collector-base voltage	$V_{CBO}$	-50	V	
Collector-emitter voltage	$V_{CEO}$	-50	V	
Emitter-base voltage	$V_{EBO}$	<b>-</b> 5	V	
Collector current	IC	-150	mA	
Base current	Ι <sub>Β</sub>	-30	mA	
Collector power dissipation	PC	150	mW	
Junction temperature	Tj	125	°C	
Storage temperature range	T <sub>stg</sub>	-55 to 125	°C	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

1. BASE
2. EMITTER
3. COLLECTOR

JEDEC TO-236MOD

JEITA SC-59

TOSHIBA 2-3F1A

Weight: 0.012 g (typ.)

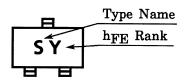
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### **Electrical Characteristics (Ta = 25°C)**

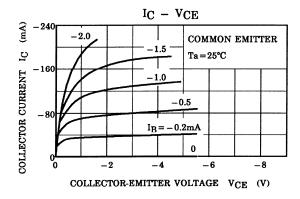
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I <sub>CBO</sub>	$V_{CB} = -50 \text{ V}, I_E = 0$	_	_	-0.1	μΑ
Emitter cut-off current	I <sub>EBO</sub>	$V_{EB} = -5 \text{ V}, I_C = 0$	-	-	-0.1	μΑ
DC current gain	h <sub>FE</sub> (Note)	$V_{CE} = -6 \text{ V}, I_C = -2 \text{ mA}$	70		400	
Collector-emitter saturation voltage	V <sub>CE (sat)</sub>	$I_C = -100 \text{ mA}, I_B = -10 \text{ mA}$	_	-0.1	-0.3	V
Transition frequency	f <sub>T</sub>	$V_{CE} = -10 \text{ V}, I_{C} = -1 \text{ mA}$	80	_	_	MHz
Collector output capacitance	C <sub>ob</sub>	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$	-	4	7	pF
Noise figure	NF	$\begin{split} &V_{CE} = -6 \text{ V, I}_{C} = -0.1 \text{ mA, f} = 1 \text{ kHz,} \\ &Rg = 10 \text{ k}\Omega, \end{split}$		1.0	10	dB

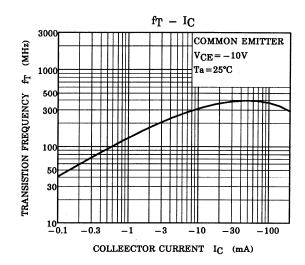
Note: hFE classification O (O): 70 to 140, Y (Y): 120 to 240, GR (G): 200 to 400, ( ) marking symbol

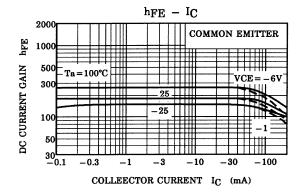
#### Marking

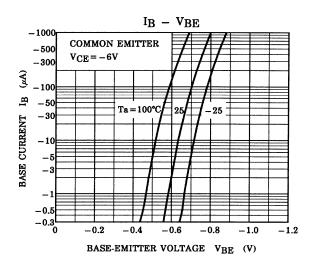


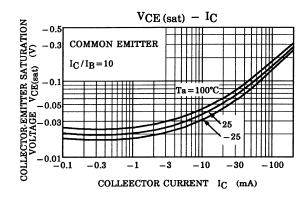
Start of commercial production 1982-12

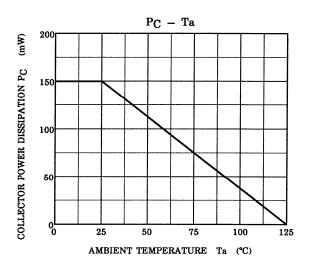












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